

Amendments to the Specification

Please amend the paragraph [0016] at page 6 of the application as follows:

Exemplary preferred methods of forming a conductive metal silicide by reaction of metal with silicon are described with reference to ~~Figs. 1-5~~ Figs. 1-6. Referring initially to Fig. 1, a substrate fragment is indicated generally with reference numeral 10, and comprises a semiconductor substrate 12. In the context of this document, the term "semiconductor substrate" or "semiconductive substrate" is defined to mean any construction comprising semiconductive material, including, but not limited to, bulk semiconductive materials such as a semiconductive wafer (either alone or in assemblies comprising other materials thereon), and semiconductive material layers (either alone or in assemblies comprising other materials). The term "substrate" refers to any supporting structure, including, but not limited to, the semiconductive substrates described above. Accordingly, semiconductor substrate 12 might comprise various structures and/or composites and/or mixtures of insulative, conductive and semiconductive materials. Regardless in the context of the invention, semiconductor substrate 12 comprises some exposed elemental silicon containing surface 14. Such might be a

substantially global surface across the entirety of the substrate being processed, or one or more isolated regions of exposed elemental silicon. For example, and by way of example only, an exposed silicon surface might constitute the outer surface of a conductive diffusion region formed of conductively doped monocrystalline or polycrystalline silicon exposed through a contact opening formed in an insulative material layer or layers. Regardless in one aspect, exposed elemental silicon containing surface 14 comprises monocrystalline silicon (including epitaxially grown silicon) and/or polycrystalline silicon. Exposed elemental silicon containing surface also or alternately might comprise silicon from a silicon-rich silicon compound.